

# **isc** Silicon PNP Power Transistor

#### **DESCRIPTION**

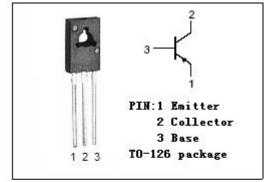
- High Collector Current -I<sub>C</sub>= -5A
- · High DC Current Gain-
  - : h<sub>FE</sub>= 150~600@I<sub>C</sub>= -1A
- · Low-Collector Saturation Voltage-
  - :  $V_{CE(sat)}$ = -0.15V(Max.)@I<sub>C</sub>= -0.5A
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

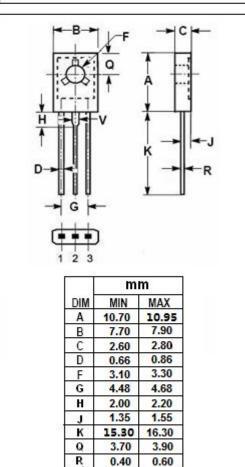
### **APPLICATIONS**

 Designed for audio frequency amplifier and switching applications.

# ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	-30	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	-30	V	
V <sub>EBO</sub>	Emitter-Base Voltage	-6	V	
Ic	Collector Current-Continuous -5		Α	
ICP	Collector Current-Pulse	-8	Α	
I <sub>B</sub>	Base Current-Continuous	-1	Α	
Pc	Collector Power Dissipation @ T <sub>C</sub> =25°C	10	W	
	Collector Power Dissipation @ T <sub>a</sub> =25°C	1		
TJ	Junction Temperature	150	$^{\circ}$	
T <sub>stg</sub>	Storage Temperature Range	-55~150	$^{\circ}$	





1.17



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2SB1657

#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CE(sat)-1</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -0.5A; I <sub>B</sub> = -25mA			-0.15	V
V <sub>CE(sat)-2</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -1A; I <sub>B</sub> = -50mA			-0.25	V
V <sub>CE(sat)-3</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -2A; I <sub>B</sub> = -0.1A			-0.4	V
V <sub>CE(sat)-4</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -3A; I <sub>B</sub> = -75mA			-1.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = -1A; I <sub>B</sub> = -50mA			-1.5	V
Ісво	Collector Cutoff Current	V <sub>CB</sub> = -30V; I <sub>E</sub> = 0			-0.1	μА
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -6V; I <sub>C</sub> = 0			-0.1	μА
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = -0.5A; V <sub>CE</sub> = -2V	150		600	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = -3A; V <sub>CE</sub> = -2V	70			
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = -50mA;V <sub>CE</sub> = -10V		75		MHz
Сов	Output Capacitance	I <sub>E</sub> =0; V <sub>CB</sub> = -10V, f <sub>test</sub> = 1MHz		60		pF

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